Unit: mm

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# **TPCC8006-H**

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- · High-speed switching
- Small gate charge: Q<sub>SW</sub> = 7.4 nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS (ON)} = 6.5 \text{ m}\Omega \text{ (typ.)} \text{ (V}_{GS} = 4.5 \text{ V)}$ 

- High forward transfer admittance:  $|Y_{fs}| = 67 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = 10 \mu A (max) (V_{DS} = 30 V)$
- Enhancement mode:  $V_{th} = 1.3$  to 2.3 V ( $V_{DS} = 10$  V,  $I_D = 0.2$  mA)

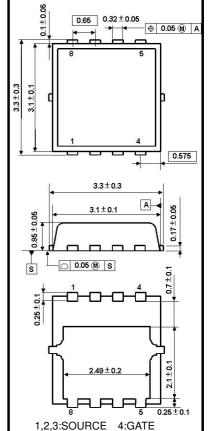
### Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	30	V
Drain-gate voltage (F	GS = 20 kΩ)	$V_{DGR}$	30	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Drain current	DC (Note 1)	ID	22	Α
Drain current	Pulsed (Note 1)	I <sub>DP</sub>	66 27	A
Drain power dissipati	on (Tc = 25°C)	$P_{D}$	27	W
Drain power dissipation	on $(t = 10 s)$ (Note 2a)	$P_{D}$	1.9	W
Drain power dissipati	on (t = 10 s) (Note 2b)	P <sub>D</sub>	0.7	W
Single-pulse avalance	ne energy (Note 3)	E <sub>AS</sub>	126	mJ
Avalanche current		I <sub>AR</sub>	22	Α
Repetitive avalanche (To	energy c = 25°C) (Note 4)	E <sub>AR</sub>	1.89	mJ
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



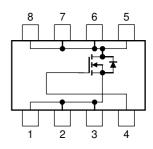
Weight: 0.02 g (typ.)

5,6,7,8:DRAIN

JEDEC JEITA TOSHIBA

## **Circuit Configuration**

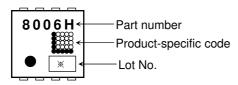
2-3X1A



#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R <sub>th (ch-c)</sub>	4.7	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R <sub>th (ch-a)</sub>	66	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b)	R <sub>th (ch-a)</sub>	180	°C/W

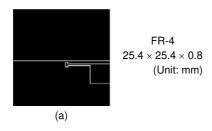
## Marking (Note 5)

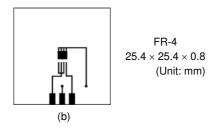


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

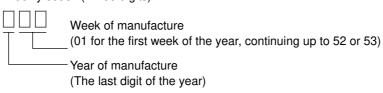




Note 3:  $V_{DD}=24~V,~T_{ch}=25^{\circ}C$  (initial),  $L=200~\mu H,~R_{G}=25~\Omega,~I_{AR}=22~A$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



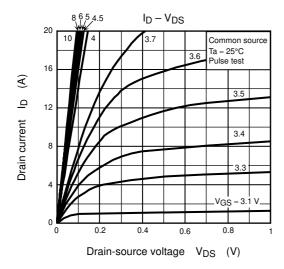
## Electrical Characteristics (Ta = 25°C)

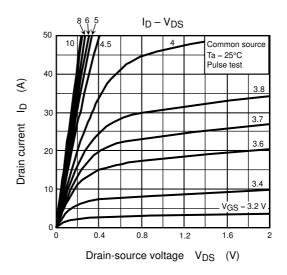
Ch	aracteristic	teristic Symbol Test Condition Min Typ.		Тур.	Max	Unit	
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	nt	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V		_	10	μА
Drain agurag bro	okdowa voltago	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V
Drain-source breakdown voltage		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_	_	V
Gate threshold voltage		V <sub>th</sub>	$V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA}$	1.3	_	2.3	٧
Drain-cource ON	resistance	D	$V_{GS} = 4.5 \text{ V}, I_D = 11 \text{ A}$		6.5	9.3	mΩ
Diain-source Oiv	resistance	nds (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 11 A	—     —     10       30     —     —       15     —     —       1.3     —     2.3       —     6.5     9.3       —     5.3     8.0       34     67     —       —     1700     2200       —     110     180       —     350     —       —     2.8     4.2       —     3.8     —	11122		
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 11 A	34	67	_	S
Input capacitance	)	C <sub>iss</sub>		_	1700	2200	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	110	180	pF
Output capacitance		Coss		_	350	_	
Gate resistance		rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$	_	2.8	4.2	Ω
$ P_{DS} = 10 \text{ V},  P_{DS} = 11 \text{ A} $ $ P_{DS} = 10 \text{ V},  P_{DS} = 11 \text{ A} $ $ P_{DS} = 10 \text{ V},  P_{DS} = 11 \text{ A} $ $ P_{DS} = 10 \text{ V},  P_{DS} = 11 \text{ A} $ $ P_{DS} = 10 \text{ V},  P_{DS} = 11 \text{ A} $ $ P_{DS} = 10 \text{ V},  P_{DS} = 11 \text{ A} $ $ P_{DS} = 10 \text{ V},  $	Rise time	t <sub>r</sub>	10 V 🔲 lp = 11 A	_	3.8	_	
	_	10	_				
Switching time	Y <sub>fs</sub>   V <sub>DS</sub> = 10 V, I <sub>D</sub> = 11 A	- ns					
	Turn-off time	t <sub>off</sub>	55	_	42	_	
Total gate charge	tal gate charge		$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 22 \text{ A}$	_	27	_	
(gate-source plus	gate-drain)	Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 22 \text{ A}$	_			nC
Gate-source charge 1		Q <sub>gs1</sub>		_	5.2	_	
Gate-drain ("Miller") charge		Q <sub>gd</sub>	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 22 \text{ A}$		4.8	_	
Gate switch charg	ge	Q <sub>SW</sub>		_	7.4	_	

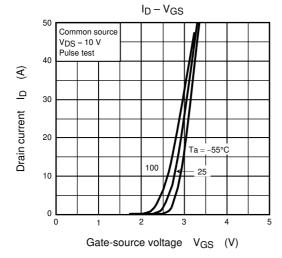
## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

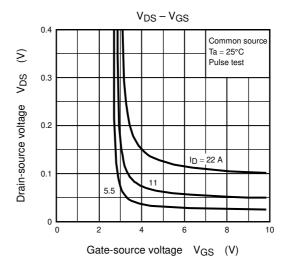
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	66	Α
Forward voltage (diode)			$V_{DSF}$	$I_{DR} = 22 \text{ A}, V_{GS} = 0 \text{ V}$		_	-1.2	V

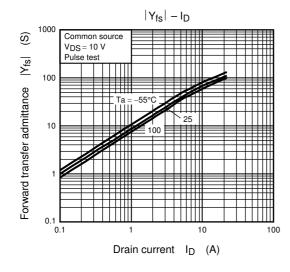
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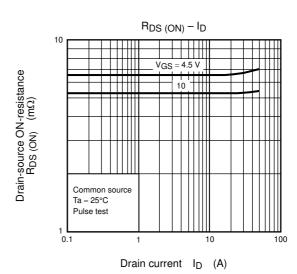




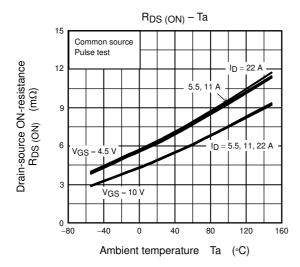


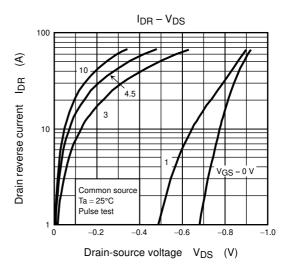


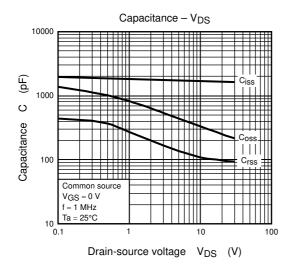


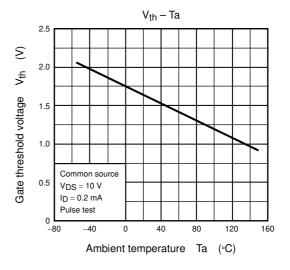


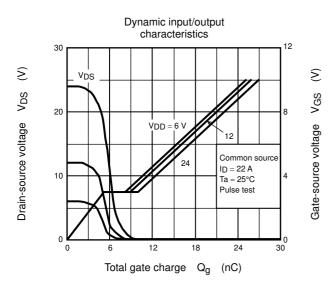
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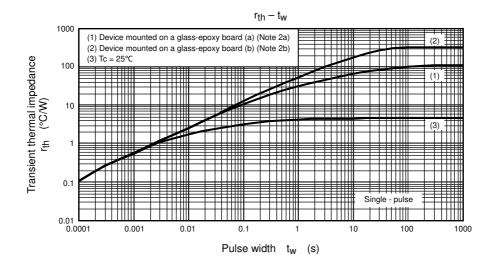


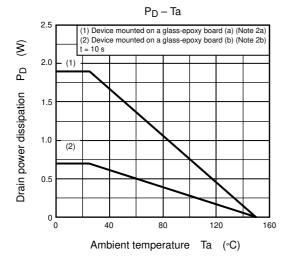


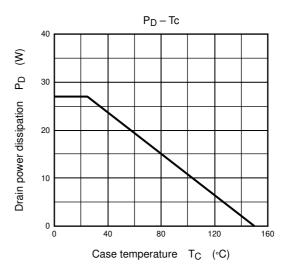


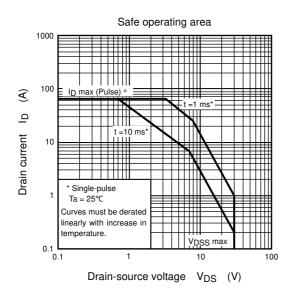


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